

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning on page 3, line 17, as follows:

~~In contrast to a pin-type photodiode such as shown in FIG. 1 in which i layer 51 for photon absorption, i.e., the depletion layer, must be provided with sufficient thickness, the depletion layer in a Schottky photodiode can be made thin, and as a result, the carrier transit time can be shortened.~~ In addition, the light absorption in the device surface layer can be effectively used in a Schottky photodiode.

Please amend the paragraph beginning on page 12, line 2 as follows:

The photodiode may further include a first electrode electrically connected to the first semiconductor layer and a second electrode electrically connected to the conductive film for applying a reverse bias voltage to form a Schottky barrier in the vicinity of the junction with the conductive film of the ~~second~~ first semiconductor layer. In addition, the thickness of the ~~second~~ first semiconductor layer interposed between the ~~[[first]]~~ second semiconductor layer and the conductive film is preferably equal to or less than the length of the bleeding of near-field light that appears on the first-surface side at the location of the aperture when light is irradiated from the ~~second~~ first surface onto the conductive film. More specifically, the thickness of the second semiconductor layer is, for example, equal to or greater than 50 nm and equal to or less than 100 nm.

Please amend the paragraph beginning on page 12, line 18, as follows:

In the photodiode of the present invention, a conductive member may be included having a dimension that is smaller than the wavelength of incident light at a location separated by a distance shorter than the wavelength of incident light from the Schottky junction composed of the ~~second~~ first semiconductor layer and the conductive film.

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Please amend the paragraph beginning on page 12, line 23, as follows:

In the photodiode of the present invention, a transparent film having substantially the same index of refraction as the ~~second~~ first semiconductor layer may be provided on the first surface of the conductive film, and further, an antireflection film for the incident light may be provided.

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